

L Number	Hits	Search Text	DB	Time stamp
1	19705	(silicon adj germanium) or sige	USPAT; US-PGPUB; JPO	2004/09/15 15:34
2	834973	carbon	USPAT; US-PGPUB; JPO	2004/09/15 15:34
3	164483	implant\$3	USPAT; US-PGPUB; JPO	2004/09/15 15:34
4	280164	strain\$4	USPAT; US-PGPUB; JPO	2004/09/15 15:34
5	12539	sti or (shallow near3 trench\$2 near3 isolat\$3)	USPAT; US-PGPUB; JPO	2004/09/15 15:35
6	21219	(carbon or "C") near2 (ion\$1 or dopant\$1 or impurit\$4)	USPAT; US-PGPUB; JPO	2004/09/15 15:36
7	1402	implant\$3 near15 ((carbon or "C") near2 (ion\$1 or dopant\$1 or impurit\$4))	USPAT; US-PGPUB; JPO	2004/09/15 16:23
8	21	((silicon adj germanium) or sige) same (implant\$3 near15 ((carbon or "C") near2 (ion\$1 or dopant\$1 or impurit\$4)))	USPAT; US-PGPUB; JPO	2004/09/15 15:37
9	6	((silicon adj germanium) or sige) same (implant\$3 near15 ((carbon or "C") near2 (ion\$1 or dopant\$1 or impurit\$4))) and strain\$4	USPAT; US-PGPUB; JPO	2004/09/15 15:37
11	15	((silicon adj germanium) or sige) same (implant\$3 near15 ((carbon or "C") near2 (ion\$1 or dopant\$1 or impurit\$4))) not (((silicon adj germanium) or sige) same (implant\$3 near15 ((carbon or "C") near2 (ion\$1 or dopant\$1 or impurit\$4))) and strain\$4)	USPAT; US-PGPUB; JPO	2004/09/15 15:47
15	21	((silicon adj germanium) or sige) same (implant\$3 near15 ((carbon or "C") near2 (ion\$1 or dopant\$1 or impurit\$4))) or (((silicon adj germanium) or sige) same (implant\$3 near15 ((carbon or "C") near2 (ion\$1 or dopant\$1 or impurit\$4))) and strain\$4) or (((silicon adj germanium) or sige) same (implant\$3 near15 ((carbon or "C") near2 (ion\$1 or dopant\$1 or impurit\$4))) not (((silicon adj germanium) or sige) same (implant\$3 near15 ((carbon or "C") near2 (ion\$1 or dopant\$1 or impurit\$4))) and strain\$4))	USPAT; US-PGPUB; JPO	2004/09/15 16:23
16	610685	gate\$1	USPAT; US-PGPUB; JPO	2004/09/15 16:23
17	225125	(mosfet\$1 or mos or fet\$1 or (field adj effect))	USPAT; US-PGPUB; JPO	2004/09/15 16:24
18	38339	nmos or n-mos pmos or p-mos	USPAT; US-PGPUB; JPO	2004/09/15 16:24
19	238778	((mosfet\$1 or mos or fet\$1 or (field adj effect))) or (nmos or n-mos pmos or p-mos)	USPAT; US-PGPUB; JPO	2004/09/15 16:25
20	174151	gate\$1 and (((mosfet\$1 or mos or fet\$1 or (field adj effect))) or (nmos or n-mos pmos or p-mos))	USPAT; US-PGPUB; JPO	2004/09/15 16:25
21	128	(implant\$3 near15 ((carbon or "C") near2 (ion\$1 or dopant\$1 or impurit\$4))) and ((silicon adj germanium) or sige)	USPAT; US-PGPUB; JPO	2004/09/15 16:25
22	86	(gate\$1 and (((mosfet\$1 or mos or fet\$1 or (field adj effect))) or (nmos or n-mos pmos or p-mos))) and ((implant\$3 near15 ((carbon or "C") near2 (ion\$1 or dopant\$1 or impurit\$4))) and ((silicon adj germanium) or sige))	USPAT; US-PGPUB; JPO	2004/09/15 16:25

23	72	((gate\$1 and (((mosfet\$1 or mos or fet\$1 or (field adj effect))) or (nmos or n-mos pmos or p-mos))) and ((implant\$3 near15 ((carbon or "C") near2 (ion\$1 or dopant\$1 or impurit\$4))) and ((silicon adj germanium) or sige))) not (((silicon adj germanium) or sige) same (implant\$3 near15 ((carbon or "C") near2 (ion\$1 or dopant\$1 or impurit\$4))) or (((silicon adj germanium) or sige) same (implant\$3 near15 ((carbon or "C") near2 (ion\$1 or dopant\$1 or impurit\$4))) and strain\$4) or (((silicon adj germanium) or sige) same (implant\$3 near15 ((carbon or "C") near2 (ion\$1 or dopant\$1 or impurit\$4))) not (((silicon adj germanium) or sige) same (implant\$3 near15 ((carbon or "C") near2 (ion\$1 or dopant\$1 or impurit\$4))) and strain\$4)))	USPAT; US-PGPUB; JPO	2004/09/15 16:25
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